

AMENDMENTS TO THE SPECIFICATION

Please replace the abstract at page 55 of the specification with the following new abstract:

ABSTRACT OF THE DISCLOSURE

A dielectric separation type semiconductor device ~~of~~ having high voltage withstanding capability includes a primary dielectric layer (3-1) on a first surface of a semiconductor substrate (1), a first conductivity type first semiconductor layer (2) ~~of first conductivity type~~ disposed oppositely to the substrate (1) with the primary dielectric layer (3-1) sandwiched, a first conductivity type second semiconductor layer (4) ~~of first conductivity type~~ on the first semiconductor layer (2), a second conductivity type third semiconductor layer (5) ~~of second conductivity type~~ surrounding peripherally the first semiconductor layer (2), a ring-like insulation film (9) surrounding peripherally the third semiconductor layer (5), a first electrode (6) on the second semiconductor layer (4), a second electrode (7) on the third semiconductor layer (5), a back-surface electrode (8) deposited on a second surface of the substrate (1), and a first auxiliary dielectric layer (3-2) disposed immediately below the second semiconductor layer (4), being junctioned to the second surface.